

WHAT IS CLAIMED IS:

1. An apparatus comprising:

a loading chamber;

a first chamber for forming a light-emitting film by a liquid jet method;

a second chamber for forming a conductive film by a sputtering method;

a third chamber for forming an insulating film by a sputtering method; and  
an unloading chamber,

wherein a substrate is so supported that an angle subtended by a surface of the  
substrate to be treated and the direction of gravity is within from 0 to 30° in all of the  
loading chamber, the first chamber to the third chamber and the unloading chamber.

2. An apparatus comprising:

a loading chamber;

a common chamber;

a first chamber for forming a light-emitting film by a liquid jet method;

a second chamber for forming a conductive film by a sputtering method;

a third chamber for forming an insulating film by a sputtering method; and  
an unloading chamber,

wherein a substrate is so supported that an angle subtended by a surface of the  
substrate to be treated and the direction of gravity is within from 0 to 30° in all of the  
loading chamber, the common chamber, the first chamber to the third chamber and the  
unloading chamber.

3. An apparatus comprising:

a loading chamber;

a first chamber for forming a light-emitting film by a printing method;

a second chamber for forming a conductive film by a sputtering method;

a third chamber for forming an insulating film by a sputtering method; and  
an unloading chamber,

wherein a substrate is so supported that an angle subtended by a surface of the  
substrate to be treated and the direction of gravity is within from 0 to 30° in all of the  
loading chamber, the first chamber to the third chamber and the unloading chamber.

4. An apparatus comprising:

a loading chamber;

a common chamber;

a first chamber for forming a light-emitting film by a printing method;

a second chamber for forming a conductive film by a sputtering method;

a third chamber for forming an insulating film by a sputtering method; and  
an unloading chamber,

wherein a substrate is so supported that an angle subtended by a surface of the  
substrate to be treated and the direction of gravity is within from 0 to 30° in all of the  
loading chamber, the common chamber, the first chamber to the third chamber and the  
unloading chamber.

5. An apparatus comprising:

- a loading chamber;  
a first chamber for forming a light-emitting film by a spray method;  
a second chamber for forming a conductive film by a sputtering method;  
a third chamber for forming an insulating film by a sputtering method; and  
5 an unloading chamber,  
wherein a substrate is so supported that an angle subtended by a surface of the  
substrate to be treated and the direction of gravity is within from 0 to 30° in all of the  
loading chamber, the first chamber to the third chamber and the unloading chamber.
- 10 6. An apparatus comprising:  
a loading chamber;  
a common chamber;  
a first chamber for forming a light-emitting film by a spray method;  
a second chamber for forming a conductive film by a sputtering method;  
15 a third chamber for forming an insulating film by a sputtering method; and  
an unloading chamber,  
wherein a substrate is so supported that an angle subtended by a surface of the  
substrate to be treated and the direction of gravity is within from 0 to 30° in all of the  
loading chamber, the common chamber, the first chamber to the third chamber and the  
20 unloading chamber.
7. An apparatus according to any one of claims 1 to 6, wherein the light-emitting  
film comprises at least one layer selected from the group consisting of a hole injection  
layer a hole-transporting layer, a hole-blocking layer, an electron injection layer, an  
25 electron-transporting layer and an electron-blocking layer.
8. An apparatus according to any one of claims 1 to 6, wherein the conductive film  
is a metal film comprising an element belong to the Group 1 or the Group 2 of periodic  
30 table.
9. An apparatus according to any one of claims 1 to 6, wherein the conductive film  
is an oxide conductive film.
10. An apparatus according to any one of claims 1 to 6, wherein the insulating film  
35 comprises silicon nitride.
11. An apparatus according to any one of claims 1 to 6, wherein the loading  
chamber and the unloading chamber are constituted as a unitary structure.
- 40 12. A method of producing a light-emitting device comprising the steps of:  
forming a light-emitting film on an electrode by an ink jet method;  
forming a conductive film on the light-emitting film by a sputtering method;  
and  
forming an insulating film on the conductive film by a sputtering method,  
45 wherein the light-emitting film forming step, the conductive film forming step  
and the insulating film forming step are carried out while holding a substrate having the

electrode in a manner that an angle subtended by a surface of the substrate and the direction of gravity is within a range of from 0 to 30° .

13. A method of producing a light-emitting device comprising the steps of:  
5 forming a light-emitting film on an electrode by a printing method;  
forming a film on the light-emitting film by a sputtering method; and  
forming an insulating film on the conductive film by a sputtering method,  
wherein the light-emitting film forming step, the conductive film forming step  
and the insulating film forming step are carried out while holding a substrate having the  
10 electrode in a manner that an angle subtended by a surface of the substrate and the  
direction of gravity is within a range of from 0 to 30° .
14. A method of producing a light-emitting device comprising the steps of:  
forming a light-emitting film on an electrode by a spray method;  
15 forming a conductive film on the light-emitting material by a sputtering method;  
and  
forming an insulating film on the conductive film by a sputtering method,  
wherein the light-emitting film forming step, the conductive film forming step  
and the insulating film forming step are carried out while holding a substrate having the  
20 electrode in a manner that an angle subtended by a surface of the substrate and the  
direction of gravity is within a range of from 0 to 30° .
15. A method of producing a light-emitting device according to any one of claims  
12 to 14, wherein the light-emitting film comprises at least one layer selected from the  
25 group consisting of a hole injection layer, a hole-transporting layer, a hole-blocking layer,  
an electron injection layer, an electron-transporting layer and an electron-blocking layer.
16. A method of producing a light-emitting device according to any one of claims  
12 to 14, wherein the conductive film is a metal film comprising an element belong to  
30 the Group 1 or the Group 2 of periodic table.
17. A method of producing a light-emitting device according to any one of claims  
12 to 14, wherein the conductive film is an oxide conductor film.
- 35 18. A method of producing a light-emitting device according to any one of claims  
12 to 14, wherein the insulating film comprises silicon nitride.